# International Rectifier

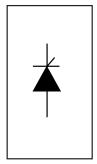
# SAFE**IR** Series 16TTS...SPbF

# SURFACE MOUNTABLE PHASE CONTROL SCR Lead-Free ("PbF" suffix)

#### **Description/Features**

The 16TTS...SPbF SAFE**IR** series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125° C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with International Rectifier input diodes, switches and output rectifiers which are available in identical package outlines.



V<sub>T</sub> < 1.4V @ 10A

 $I_{TCM} = 200A$ 

 $V_{DDM} = 800V - 1200V$ 

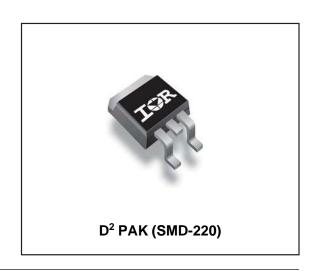
#### **Output Current in Typical Applications**

Applications	Single-phase Bridge	Three-phase Bridge	Units
NEMAFR-4orG10glassfabric-basedepoxy with4oz(140μm)copper	2.5	3.5	
Aluminum IMS, R <sub>thCA</sub> =15°C/W	6.3	9.5	Α
AluminumIMS with heatsink, R <sub>thCA</sub> =5°C/W	14.0	18.5	

 $T_A = 55$ °C,  $T_J = 125$ °C, footprint 300mm<sup>2</sup>

#### **Major Ratings and Characteristics**

Characteristics	Values	Units
I <sub>T(AV)</sub> Sinusoidal waveform	10	Α
I <sub>RMS</sub>	16	Α
V <sub>RRM</sub> /V <sub>DRM</sub>	800-1200	V
I <sub>TSM</sub>	200	Α
V <sub>T</sub> @16A,T <sub>J</sub> =25°C	1.4	V
dv/dt	500	V/µs
di/dt	150	A/µs
T <sub>J</sub>	-40 to 125	°C





# Voltage Ratings

Part Number	V <sub>RRM</sub> , maximum peak reverse voltage V	V <sub>DRM</sub> , maximum peak direct voltage V	I <sub>RRM</sub> /I <sub>DRM</sub> 125°C mA
16TTS08S	800	800	10
16TTS12S	1200	1200	10

# Absolute Maximum Ratings

	Parameters	16T	TSS	Units		Conditions
<u> </u>						
I <sub>T(AV)</sub>	Max.AverageOn-stateCurrent	1	0	Α	@1 <sub>c</sub> =93°C,18	30° conduction half sine wave
I <sub>RMS</sub>	Max.RMSOn-stateCurrent	1	6			
I <sub>TSM</sub>	Max.PeakOneCycleNon-Repetitive	17	70		10msSinepuls	e,ratedV <sub>RRM</sub> applied
	SurgeCurrent	20	00		10msSinepulse	e,novoltagereapplied
I <sup>2</sup> t	Max.I <sup>2</sup> tforfusing	14	14	A <sup>2</sup> s	10msSinepuls	e,ratedV <sub>RRM</sub> applied
		20	00		10msSinepulse	e,novoltagereapplied
I <sup>2</sup> √t	Max.I <sup>2</sup> √tforfusing	20	2000		t=0.1to10ms,novoltagereapplied	
V <sub>TM</sub>	Max.On-stateVoltageDrop	1.4		V	@ 16A, T <sub>J</sub> = 25°C	
r <sub>t</sub>	On-state slope resistance	24.0		mΩ	T <sub>J</sub> = 125°C	
V <sub>T(TO)</sub>	Threshold Voltage	1.1		V		
I <sub>RM</sub> /I <sub>DM</sub>	Max.Reverse and Direct	0.	0.5		T <sub>J</sub> = 25 °C	V = rated V / V
	Leakage Current	1	0		T <sub>J</sub> = 125 °C	$V_R = rated V_{RRM} / V_{DRM}$
I <sub>H</sub>	Holding Current	Тур.	Max.		Anode Supply	= 6V, Resistive load, Initial I <sub>T</sub> =1A
			100	mA		
IL	Max. Latching Current	200		mA	Anode Supply	= 6V, Resistive load
dv/dt	Max. Rate of Rise of off-state Voltage	500		V/µs		
di/dt	Max. Rate of Rise of turned-on Current	150		A/µs		

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# Triggering

	Parameters	16TTSS	Units	Conditions
P <sub>GM</sub>	Max. peak Gate Power	8.0	W	
P <sub>G(AV)</sub>	Max. average Gate Power	2.0		
+ I <sub>GM</sub>	Max. paek positive Gate Current	1.5	Α	
- V <sub>GM</sub>	Max. paek negative Gate Voltage	10	V	
I <sub>GT</sub>	Max. required DC Gate Current	90	mA	Anode supply = 6V, resistive load, T <sub>J</sub> = - 10°C
	to trigger	60		Anode supply = 6V, resistive load, T <sub>J</sub> = 25°C
		35		Anode supply = 6V, resistive load, T <sub>J</sub> = 125°C
V <sub>GT</sub>	Max. required DC Gate Voltage	3.0	V	Anode supply = 6V, resistive load, T <sub>J</sub> = - 10°C
	to trigger	2.0		Anode supply = 6V, resistive load, T <sub>J</sub> = 25°C
		1.0		Anode supply = 6V, resistive load, T <sub>J</sub> = 125°C
$V_{GD}$	Max. DC Gate Voltage not to trigger	0.25		T <sub>J</sub> = 125°C, V <sub>DRM</sub> = rated value
$I_{GD}$	Max. DC Gate Current not to trigger	2.0	mA	$T_J$ = 125°C, $V_{DRM}$ = rated value

# Switching

	Parameters	16TTSS	Units	Conditions
t <sub>gt</sub>	Typical turn-on time	0.9	μs	$T_J = 25$ °C
t <sub>rr</sub>	Typical reverse recovery time	4		T <sub>J</sub> = 125°C
t <sub>q</sub>	Typical turn-off time	110		

# Thermal-Mechanical Specifications

	Parameters	16TTSS	Units	Conditions
T <sub>J</sub>	Max. Junction Temperature Range	-40 to 125	°C	
T <sub>stg</sub>	Max. Storage Temperature Range	-40 to 125	°C	
	Soldering Temperature	240	°C	for 10 seconds (1.6mm from case)
R <sub>thJC</sub>	Max.ThermalResistanceJunction	1.3	°C/W	DCoperation
	to Case			
R <sub>thJA</sub>	Typ. Thermal Resistance Junction	40	°C/W	
	to Ambient (PCB Mount)**			
wt	Approximate Weight	2 (0.07)	g(oz.)	
Т	Case Style	D <sup>2</sup> Pak (SMD-220)		

<sup>\*\*</sup> When mounted on 1" square (650mm²) PCB of FR-4 or G-10 material 4 oz (140 $\mu$ m) copper 40°C/W For recommended footprint and soldering techniques refer to application note #AN-994

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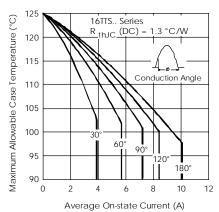


Fig. 1 - Current Rating Characteristics

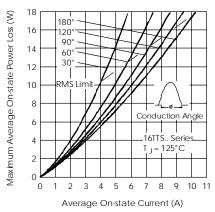


Fig. 3 - On-state Power Loss Characteristics

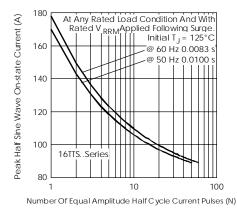


Fig. 6 - Maximum Non-Repetitive Surge Current

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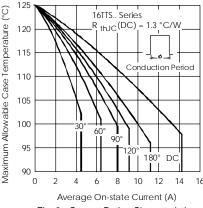


Fig. 2 - Current Rating Characteristics

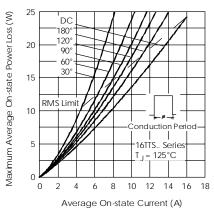


Fig. 4 - On-state Power Loss Characteristics

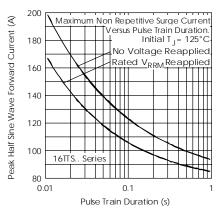


Fig. 7 - Maximum Non-Repetitive Surge Current

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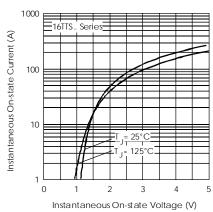


Fig. 7 - On-state Voltage Drop Characteristics

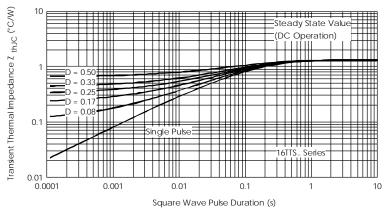


Fig. 8 - Thermal Impedance  $Z_{\rm thJC}$  Characteristics

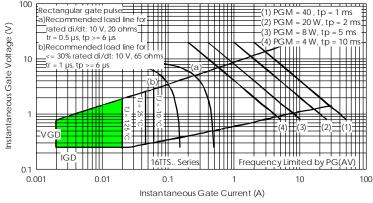
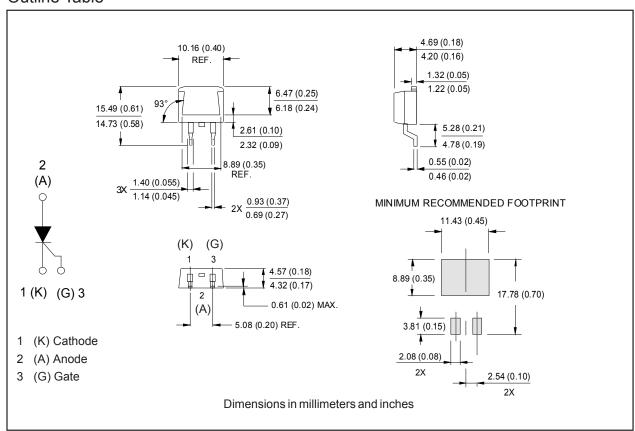
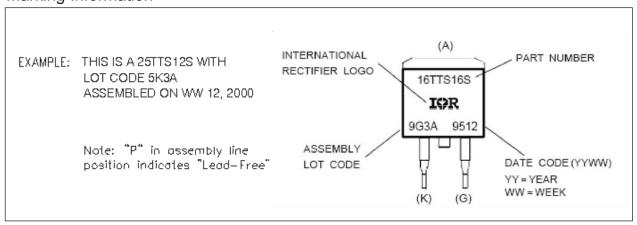


Fig. 9 - Gate Characteristics

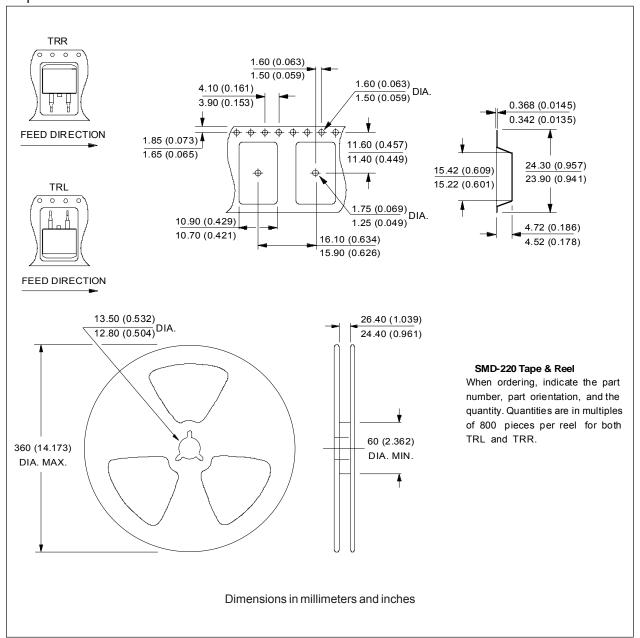
#### **Outline Table**



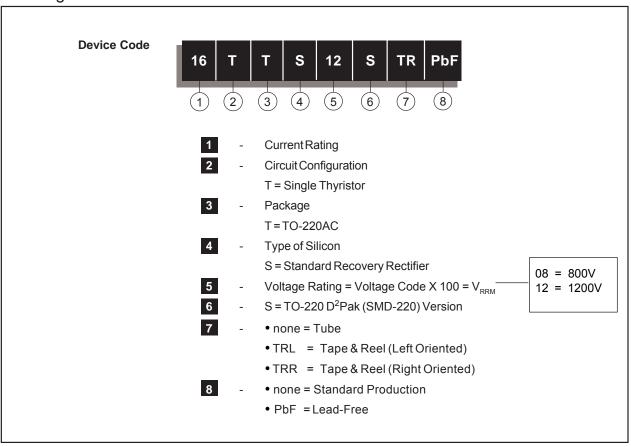
#### Marking Information



Tape & Reel Information



#### Ordering Information Table



Data and specifications subject to change without notice. This product has been designed and qualified for Industrial Level and Lead-Free.

Qualification Standards can be found on IR's Web site.



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